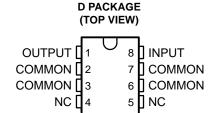
- 3-Terminal Regulators
- Output Current up to 100 mA
- No External Components
- Internal Thermal-Overload Protection
- Internal Short-Circuit Current Limiting
- Direct Replacements for Fairchild μA78L00 Series

#### description

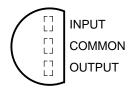
This series of fixed-voltage integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. In addition, they can be used with power-pass elements to make high-current voltage regulators. One of these regulators can deliver up to 100 mA of output current. The internal limiting and thermal-shutdown features of these regulators essentially make them immune to overload. When used as a replacement for a zener diode-resistor combination, an effective improvement in output impedance can be obtained, together with lower bias current.

The  $\mu$ A78L00C and  $\mu$ A78L00AC series are characterized for operation over the virtual junction temperature range of 0°C to 125°C. The  $\mu$ A78L05AI is characterized for operation over the virtual junction temperature range of -40°C to 125°C.



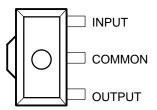
NC - No internal connection

# LP PACKAGE (TOP VIEW)



PK PACKAGE (TOP VIEW)

TO-226AA



The center lead is in electrical contact with the tab.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

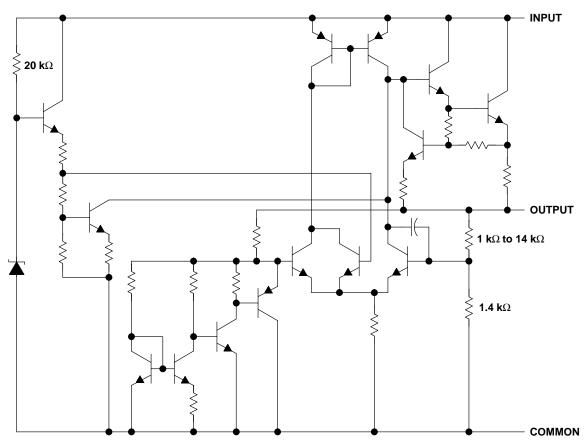


#### **AVAILABLE OPTIONS**

			PACKAGE									
TJ	VO(NOM)	SMALL O	_	PLASTIC CYI (LP	-	SOT-89 (PK)						
	(V)			OUTPUT VOLTA	GE TOLERANC	Ē						
		5%	10%	5%	10%	5%	10%					
	2.6	μΑ78L02ACD	-	μΑ78L02ACLP	1	1	_					
	5	μA78L05ACD	μΑ78L05CD	μA78L05ACLP	μΑ78L05CLP	μΑ78L05ACPK	μΑ78L05CPK					
0°C	6.2	_	_	μΑ78L06ACLP	_	μΑ78L06ACPK	_					
to	8	μΑ78L08ACD	μΑ78L08CD	μΑ78L08ACLP	-	μΑ78L08ACPK	μΑ78L08CPK					
125°C	9	μΑ78L09ACD	_	μΑ78L09ACLP	μΑ78L09CLP	μΑ78L09ACPK	_					
123 C	10	μΑ78L10ACD	_	μΑ78L10ACLP	_	μΑ78L10ACPK	_					
	12	μΑ78L12ACD	_	μΑ78L12ACLP	-	μΑ78L12ACPK	_					
	15	μΑ78L15ACD	_	μΑ78L15ACLP	-	μΑ78L15ACPK	_					
-40°C												
to 125°C	5	-	-	μΑ78L05AILP	-	-	-					

D and LP packages are available taped and reeled. Add the suffix R to the device type (e.g.,  $\mu$ A78L05ACDR). The PK package is only available taped and reeled (do not add the suffix R to the device type).

#### schematic



NOTE A: Resistor values shown are nominal.



## absolute maximum ratings over virtual junction temperature range (unless otherwise noted)†

Input voltage, V <sub>I</sub> : μΑ78L02AC, μΑ78L05C–μΑ78L09C, μΑ78L10AC	30 V
μΑ78L12C, μΑ78L12AC, μΑ78L15C, μΑ78L15AC	35 V
Package thermal impedance, θ <sub>JA</sub> (see Notes 1 and 2): D package	97°C/W
LP package	156°C/W
PK package	52°C/W
Virtual junction temperature, T <sub>J</sub>	150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
Storage temperature range, T <sub>stg</sub>	-65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. Maximum power dissipation is a function of T<sub>J</sub>(max), θ<sub>JA</sub>, and T<sub>A</sub>. The maximum allowable power dissipation at any allowable ambient temperature is P<sub>D</sub> = (T<sub>J</sub>(max) T<sub>A</sub>)/θ<sub>JA</sub>. Operating at the absolute maximum T<sub>J</sub> of 150°C can affect reliability. Due to variations in individual device electrical characteristics and thermal resistance, the built-in thermal-overload protection may be activated at power levels slightly above or below the rated dissipation.
  - 2. The package thermal impedance is calculated in accordance with JESD 51-7.

### recommended operating conditions

			MIN	MAX	UNIT
		μΑ78L02AC	4.75	20	
		μΑ78L05C, μΑ78L05AC	7	20	
		μΑ78L06C, μΑ78L06AC	8.5	20	
ν.	land to take me	μΑ78L08C, μΑ78L08AC	10.5	23	V
۷Į	Input voltage  µA78L09C, µA78L09AC		11.5	24	V
		μΑ78L10AC	12.5	25	
		μΑ78L12C, μΑ78L12AC	14.5	27	
		μΑ78L15C, μΑ78L15AC	17.5	30	
lo	Output current	-		100	mA
т.	Operating virtual junction temperature range	μΑ78LxxC and μΑ78LxxAC series	0	125	°C
TJ	Operating virtual junction temperature range	μΑ78L05AI	-40	125	



### electrical characteristics at specified virtual junction temperature, $V_I$ = 9 V, $I_O$ = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	-+	μ <b>Α</b>	78L02A	С	UNIT
PARAMETER	TEST CONDITIONS	Τ <sub>J</sub> †	MIN	TYP	MAX	UNIT
	\\. 4.75\\\ to 20\\\. \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	25°C	2.5	2.6	2.7	
Output voltage	$V_I = 4.75 \text{ V to } 20 \text{ V}, \qquad I_O = 1 \text{ mA to } 40 \text{ m}$	0°C to 125°C	2.45		2.75	V
	I <sub>O</sub> = 1 mA to 70 mA	0°C to 125°C	2.45		2.75	
Input voltage regulation	V <sub>I</sub> = 4.75 V to 20 V	25°C		20	100	mV
Input voltage regulation	V <sub>I</sub> = 5 V to 20 V	25°C		16	75	IIIV
Ripple rejection	$V_1 = 6 \text{ V to } 20 \text{ V}, \qquad f = 120 \text{ Hz}$	25°C	43	51		dB
Output voltage regulation	I <sub>O</sub> = 1 mA to 100 mA	25°C		12	50	mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	25 0		6	25	1117
Output noise voltage	f = 10 Hz to 100 kHz	25°C		30		μV
Dropout voltage		25°C		1.7		V
Bias current		25°C		3.6	6	mA
Dias current		125°C			5.5	ША
Bias current change	V <sub>I</sub> = 5 V to 20 V	0°C to 125°C			2.5	mA
bias current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0 0 10 125 0			0.1	IIIA

<sup>†</sup> Pulse-testing techniques maintain T<sub>J</sub> as close to T<sub>A</sub> as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

### electrical characteristics at specified virtual junction temperature, $V_I$ = 10 V, $I_O$ = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TJ‡	μ <b>Α78L05C</b>				78L05A \78L05A		UNIT	
		_	MIN	TYP	MAX	MIN	TYP	MAX		
	7 / 7 / 40 00 / 1	25°C	4.6	5	5.4	4.8	5	5.2		
Output voltage	$V_I = 7 \text{ V to } 20 \text{ V}, \qquad I_O = 1 \text{ mA to } 40 \text{ mA}$	Full range	4.5		5.5	4.75		5.25	V	
	I <sub>O</sub> = 1 mA to 70 mA	Full range	4.5		5.5	4.75		5.25		
Input voltage regulation	V <sub>I</sub> = 7 V to 20 V	2500		32	200		32	150	\/	
	V <sub>I</sub> = 8 V to 20 V	25°C		26	150		26	100	mV	
Ripple rejection	V <sub>I</sub> = 8 V to 18 V, f = 120 Hz	25°C	40	49		41	49		dB	
Output	I <sub>O</sub> = 1 mA to 100 mA	25°C		15	60		15	60	mV	
voltage regulation	I <sub>O</sub> = 1 mA to 40 mA			8	30		8	30	] ""	
Output noise voltage	f = 10 Hz to 100 kHz	25°C		42			42		μV	
Dropout voltage		25°C		1.7			1.7		V	
Bias current		25°C		3.8	6		3.8	6	mA	
bias current		125°C			5.5			5.5	IIIA	
Bias	V <sub>I</sub> = 8 V to 20 V	Eull rongs			1.5			1.5	1	
current change	I <sub>O</sub> = 1 mA to 40 mA	Full range			0.2			0.1	mA	

<sup>‡</sup> Pulse-testing techniques maintain T<sub>J</sub> as close to T<sub>A</sub> as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33- $\mu$ F capacitor across the input and a 0.1- $\mu$ F capacitor across the output. Full range for the  $\mu$ A78L05AC is T<sub>J</sub> = 0°C to 125°C and full range for the  $\mu A78L05AI$  is  $T_J = -40^{\circ}C$  to  $125^{\circ}C$ .



# electrical characteristics at specified virtual junction temperature, $V_I$ = 12 V, $I_O$ = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.1	μ	478L060	;	μ <b>Α</b>	78L06A	С	UNIT	
PARAMETER	TEST CONDITIONS	TJ <sup>†</sup>	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
	V 05 V to 20 V 1 - 4 m 4 to 40 m 4	25°C	5.7	6.2	6.7	5.95	6.2	6.45		
Output voltage	$V_{\rm I} = 8.5 \text{ V to } 20 \text{ V},  I_{\rm O} = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	5.6		6.8	5.9		6.5	V	
	I <sub>O</sub> = 1 mA to 70 mA	0°C to 125°C	5.6		6.8	5.9		6.5		
Input	V <sub>I</sub> = 8.5 V to 20 V	25°C		35	200		35	175	mV	
voltage regulation	V <sub>I</sub> = 9 V to 20 V	25°C		29	150		29	125	IIIV	
Ripple rejection	V <sub>I</sub> = 10 V to 20 V, f = 120 Hz	25°C	39	48		40	48		dB	
Output	I <sub>O</sub> = 1 mA to 100 mA	25°C		16	80		16	80	mV	
voltage regulation	I <sub>O</sub> = 1 mA to 40 mA	25°C		9	40		9	40	1117	
Output noise voltage	f = 10 Hz to 100 kHz	25°C		46			46		μV	
Dropout voltage		25°C		1.7			1.7		V	
Bias current		25°C		3.9	6		3.9	6	mA	
Dias current		125°C			5.5			5.5	ША	
Bias	V <sub>I</sub> = 9 V to 20 V	0°C to 125°C			1.5			1.5	4	
current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0 0 10 125 0			0.2			0.1	mA	

<sup>†</sup> Pulse-testing techniques maintain T<sub>J</sub> as close to T<sub>A</sub> as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

# electrical characteristics at specified virtual junction temperature, $V_I$ = 14 V, $I_O$ = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.t	μ	478L080	;	μ <b>Α</b>	78L08A	С	UNIT	
PARAMETER	TEST CONDITIONS	T <sub>J</sub> †	MIN	TYP	MAX	MIN	TYP MAX  7 8 8.3 6 8.4 6 8.4 6 8.4 7 46 0 18 80 10 40 54 µ	UNII		
	V 40.5 V/42.02 V 1 4 mA 42.40 mA	25°C	7.36	8	8.64	7.7	8	8.3		
Output voltage	$V_I = 10.5 \text{ V to } 23 \text{ V},  I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	7.2		8.8	7.6		8.4	V	
	I <sub>O</sub> = 1 mA to 70 mA	0°C to 125°C	7.2		8.8	7.6		8.4		
Input voltage regulation	V <sub>I</sub> = 10.5 V to 23 V	25°C		42	200		42	175	mV	
	V <sub>I</sub> = 11 V to 23 V	25 C		36	150		36	125	IIIV	
Ripple rejection	V <sub>I</sub> = 13 V to 23 V, f = 120 Hz	25°C	36	46		37	46		dB	
Output voltage	I <sub>O</sub> = 1 mA to 100 mA	25°C		18	80		18	80	mV I	
regulation	I <sub>O</sub> = 1 mA to 40 mA	25 C		10	40		10	40		
Output noise voltage	f = 10 Hz to 100 kHz	25°C		54			54		μV	
Dropout voltage		25°C		1.7			1.7		V	
Bias current		25°C		4	6		4	6	mA	
bias current		125°C			5.5			5.5	IIIA	
Bias	V <sub>I</sub> = 5 V to 20 V	0°C to 105°C			1.5			1.5		
current change	I <sub>O</sub> = 1 mA to 40 mA	0°C to 125°C			0.2			0.1	mA	

<sup>†</sup> Pulse-testing techniques maintain T<sub>J</sub> as close to T<sub>A</sub> as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



### electrical characteristics at specified virtual junction temperature, $V_I$ = 16 V, $I_O$ = 40 mA (unless otherwise noted)

DADAMETER	TEST CONDITIONS	t	μ	478L090	;	μ <b>Α</b>	78L09A	С	UNIT
PARAMETER	TEST CONDITIONS	TJ <sup>†</sup>	MIN	TYP	MAX	MIN	TYP	MAX	UNII
	V 40 V 12 04 V 1 4 22 4 22 4 22 4	25°C	8.3	9	9.7	8.6	9	9.4	
Output voltage	$V_I = 12 \text{ V to } 24 \text{ V},  I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	8.1		9.9	8.55		9.45	V
	I <sub>O</sub> = 1 mA to 70 mA	0°C to 125°C	8.1		9.9	8.55		9.45	
Input voltage regulation	V <sub>I</sub> = 12 V to 24 V	25°C		45	225		45	175	mV
	V <sub>I</sub> = 13 V to 24 V	25°C		40	175		40	125	IIIV
Ripple rejection	V <sub>I</sub> = 15 V to 25 V, f = 120 Hz	25°C	36	45		38	45		dB
Output	I <sub>O</sub> = 1 mA to 100 mA	25°C		19	90		19	90	mV
voltage regulation	I <sub>O</sub> = 1 mA to 40 mA	25°C		11	40		11	40	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		58			58		μV
Dropout voltage		25°C		1.7			1.7		V
Dies surrent		25°C		4.1	6		4.1	6	A
Bias current		125°C			5.5			5.5	mA
Bias	V <sub>I</sub> = 13 V to 24 V	0°C to 125°C			1.5			1.5	mΛ
current change	I <sub>O</sub> = 1 mA to 40 mA	0°C to 125°C			0.2			0.1	mA

<sup>†</sup> Pulse-testing techniques maintain TJ as close to TA as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

### electrical characteristics at specified virtual junction temperature, $V_I$ = 14 V, $I_O$ = 40 mA (unless otherwise noted)

PARAMETER	TEST C	ONDITIONS	- +	μΑ	78L10A	С	UNIT
PARAMETER	IESI C	ONDITIONS	T <sub>J</sub> †	MIN	TYP	MAX	UNIT
	V 42.V to 25.V	l - 1 m Λ to 10 m Λ	25°C	9.6	10	10.4	
Output voltage	$V_{I} = 13 \text{ V to } 25 \text{ V},$	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	9.5		10.5	V
	$I_O = 1 \text{ mA to } 70 \text{ mA}$		0°C to 125°C	9.5		10.5	
Input voltage regulation	V <sub>I</sub> = 13 V to 25 V		25°C		51	175	mV
Input voltage regulation	V <sub>I</sub> = 14 V to 25 V		25 C		42	125	IIIV
Ripple rejection	$V_{I} = 15 \text{ V to } 25 \text{ V},$	f = 120 Hz	25°C	37	44		dB
Output voltage regulation	I <sub>O</sub> = 1 mA to 100 mA		25°C		20	90	mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		25 0		11	40	1117
Output noise voltage	f = 10 Hz to 100 kHz		25°C		62		μV
Dropout voltage			25°C		1.7		V
Bias current			25°C		4.2	6	mA
Dias current			125°C			5.5	IIIA
Bias current change	V <sub>I</sub> = 14 V to 25 V	V <sub>I</sub> = 14 V to 25 V				1.5	mΑ
bias current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$		0°C to 125°C			0.1	IIIA

<sup>†</sup> Pulse-testing techniques maintain T<sub>J</sub> as close to T<sub>A</sub> as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



# electrical characteristics at specified virtual junction temperature, $V_I$ = 19 V, $I_O$ = 40 mA (unless otherwise noted)

DADAMETER	TEST CONDITIONS	t	μ	478L120	;	μ <b>Α</b>	78L12A	С	UNIT
PARAMETER	TEST CONDITIONS	TJ <sup>†</sup>	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	V 44 V (2 07 V ) 4 2 2 4 2 4 2 2 4	25°C	11.1	12	12.9	11.5	12	12.5	
Output voltage	$V_I = 14 \text{ V to } 27 \text{ V},  I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	10.8		13.2	11.4		12.6	V
	I <sub>O</sub> = 1 mA to 70 mA	0°C to 125°C	10.8		13.2	11.4		12.6	
Input voltage regulation	V <sub>I</sub> = 14.5 V to 27 V	25°C		55	250		55	250	mV
	V <sub>I</sub> = 16 V to 27 V	25°C		49	200		49	200	IIIV
Ripple rejection	V <sub>I</sub> = 15 V to 25 V, f = 120 Hz	25°C	36	42		37	42		dB
Output	I <sub>O</sub> = 1 mA to 100 mA	25°C		22	100		22	100	mV
voltage regulation	I <sub>O</sub> = 1 mA to 40 mA	25 C		13	50		13	50	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		70			70		μV
Dropout voltage		25°C		1.7			1.7		V
Bias current		25°C		4.3	6.5		4.3	6.5	mA
bias current		125°C			6			6	ША
Bias	V <sub>I</sub> = 16 V to 27 V	0°C to 125°C			1.5			1.5	mA
current change	I <sub>O</sub> = 1 mA to 40 mA	0 0 10 125 0			0.2			0.1	IIIA

<sup>†</sup> Pulse-testing techniques maintain T<sub>J</sub> as close to T<sub>A</sub> as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

# electrical characteristics at specified virtual junction temperature, $V_I$ = 23 V, $I_O$ = 40 mA (unless otherwise noted)

DADAMETED	TEST COMPITIONS	t	μ.	A78L150	;	μ <b>Α</b>	78L15A	.c	UNIT
PARAMETER	TEST CONDITIONS	T <sub>J</sub> †	MIN	TYP	MAX	MIN	TYP	MAX	UNII
	V. 47.5 V to 20 V	25°C	13.8	15	16.2	14.4	15	15.6	
Output voltage	$V_{\rm I} = 17.5 \text{ V to } 30 \text{ V}, \qquad I_{\rm O} = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	13.5		16.5	14.25		15.75	V
voltago	$I_O = 1 \text{ mA to } 70 \text{ mA}$	0°C to 125°C	13.5		16.5	14.25		15.75	
Input	V <sub>I</sub> = 17.5 V to 30 V			65	300		65	300	\/
voltage regulation	V <sub>I</sub> = 20 V to 30 V	25°C		58	250		58	250	m۷
Ripple rejection	V <sub>I</sub> = 18.5 V to 28.5 V, f = 120 Hz	25°C	33	39		34	39		dB
Output	I <sub>O</sub> = 1 mA to 100 mA	25°C		25	150		25	150	mV
voltage regulation	I <sub>O</sub> = 1 mA to 40 mA			15	75		15	75	] ""
Output noise voltage	f = 10 Hz to 100 kHz	25°C		82			82		μV
Dropout voltage		25°C		1.7			1.7		٧
Bias current		25°C		4.6	6.5		4.6	6.5	m 1
bias current		125°C			6			6	mA
Bias	V <sub>I</sub> = 10 V to 30 V	0°C to 125°C			1.5			1.5	mA
current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0 0 10 125 0			0.2			0.1	IIIA

<sup>†</sup> Pulse-testing techniques maintain T<sub>J</sub> as close to T<sub>A</sub> as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



### **APPLICATION INFORMATION**

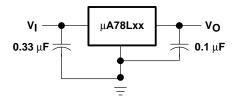


Figure 1. Fixed-Output Regulator

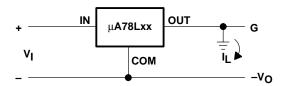


Figure 2. Positive Regulator in Negative Configuration (V<sub>I</sub> Must Float)

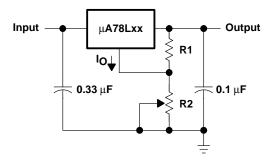


Figure 3. Adjustable-Output Regulator

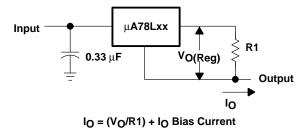


Figure 4. Current Regulator

#### **APPLICATION INFORMATION**

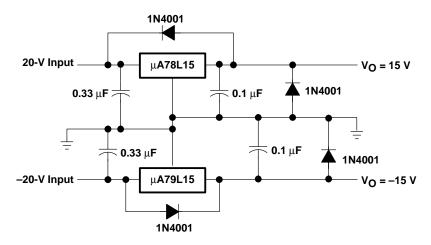


Figure 5. Regulated Dual Supply

#### operation with a load common to a voltage of opposite polarity

In many cases, a regulator powers a load that is not connected to ground, but instead, is connected to a voltage source of opposite polarity (e.g., operational amplifiers, level-shifting circuits, etc.). In these cases, a clamp diode should be connected to the regulator output as shown in Figure 6. This protects the regulator from output polarity reversals during startup and short-circuit operation.

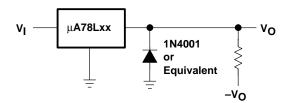


Figure 6. Output Polarity-Reversal-Protection Circuit

#### reverse-bias protection

Occasionally, the input voltage to the regulator can collapse faster than the output voltage. This can occur, for example, when the input supply is crowbarred during an output overvoltage condition. If the output voltage is greater than approximately 7 V, the emitter-base junction of the series-pass element (internal or external) could break down and be damaged. To prevent this, a diode shunt can be employed as shown in Figure 7.

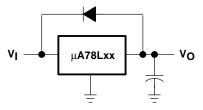


Figure 7. Reverse-Bias-Protection Circuit

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